# Abstracts

## A 6GHz-25W GaAs MESFET with an Experimentally Optimized Pattern

*A. Higashisaka, K. Honjo, Y. Takayama and F. Hasegawa. "A 6GHz-25W GaAs MESFET with an Experimentally Optimized Pattern." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 9-11.*

A high power GaAs MESFET with a high packing density has been developed by optimizing the gate finger width. The developed power MESFET is the crossover structure and has a total gate width of 15 mm in a 2.2 mm wide chip. The output powers of 25 W at 6 GHz and 20 W at 8 GHz were obtained with 3 dB associated gain from the internally matched four chip devices.

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